## 1-to-2 Decoder/ Demultiplexer <br> NL7SZ19

The NL7SZ19 is a 1 -to-2 decoder. When the output enable $(\overline{\mathrm{E}})$ is Low, the device passes data at input A to outputs Y0 (true) and Y1 (complement). The NL7SZ19 can also be used as a 1-to-2 demultiplexer. As a demultiplexer, data at input E is routed to either Y0 or Y1 depending on the state of A. The device operates over the voltage range from 1.65 V to 5.5 V .

## Features

- Designed for 1.65 V to $5.5 \mathrm{~V}_{\mathrm{CC}}$ Operation
- $2.7 \mathrm{~ns}_{\mathrm{t}}$ at $\mathrm{V}_{\mathrm{CC}}=5 \mathrm{~V}$ (Typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I IOFF Supports Partial Power Down Protection
- Source/Sink 32 mA at 5.0 V
- Available in SC-88, SC-74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant


SC-88
DF SUFFIX SC-74 UDFN6, 1.2x1.0, 0.4P CASE 419B CASE 318F-05 CASE 517AA-01

MARKING DIAGRAMS

(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION
See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.


Figure 1. Pinout (Top View)

PIN ASSIGNMENT

| Pin | Function |
| :---: | :---: |
| 1 | A |
| 2 | GND |
| 3 | E |
| 4 | $\mathrm{Y}_{1}$ |
| 5 | $\mathrm{~V}_{\mathrm{CC}}$ |
| 6 | $\mathrm{Y}_{0}$ |

FUNCTION TABLE

| $\bar{E}$ | $\mathbf{A}$ | $\mathbf{Y}_{\mathbf{0}}=\mathbf{A}+\overline{\mathbf{E}}$ | $\mathbf{Y}_{\mathbf{1}}=\overline{\mathbf{A}}+\overline{\mathbf{E}}$ |
| :---: | :---: | :---: | :---: |
| L | L | L | $H$ |
| L | $H$ | $H$ | L |
| $H$ | $H$ | $H$ | $H$ |
| $H$ | L | $H$ | $H$ |

MAXIMUM RATINGS

| Symbol | Characteristics | Value | Unit |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage NLV | $\begin{aligned} & -0.5 \text { to }+7.0 \\ & -0.5 \text { to }+6.5 \end{aligned}$ | V |
| $\mathrm{V}_{\text {IN }}$ | DC Input Voltage NLV | $\begin{aligned} & -0.5 \text { to }+7.0 \\ & -0.5 \text { to }+6.5 \end{aligned}$ | V |
| $\mathrm{V}_{\text {OUT }}$ | Active-Mode (High or Low State) <br> Tri-State Mode (Note 1) <br> Power-Down Mode (VCC $=0 \mathrm{~V}$ ) | $\begin{gathered} -0.5 \text { to } \mathrm{V}_{\mathrm{cc}}+0.5 \\ -0.5 \text { to }+7.0 \\ -0.5 \text { to }+7.0 \end{gathered}$ | V |
| $V_{\text {OUT }}$ | DC Output Voltage <br> Active-Mode (High or Low State) <br> Tri-State Mode (Note 1) <br> Power-Down Mode $\left(\mathrm{V}_{\mathrm{CC}}=0 \mathrm{~V}\right)$ | $\begin{gathered} -0.5 \text { to } V_{\mathrm{Cc}}+0.5 \\ -0.5 \text { to }+6.5 \\ -0.5 \text { to }+6.5 \end{gathered}$ | V |
| $\mathrm{IIK}^{\text {K }}$ | DC Input Diode Current $\quad \mathrm{V}_{\text {IN }}<$ GND | -50 | mA |
| lok | DC Output Diode Current $\quad \mathrm{V}_{\text {OUT }}<$ GND | -50 | mA |
| Iout | DC Output Source/Sink Current | $\pm 50$ | mA |
| $\mathrm{I}_{\text {CC }}$ or I IGND | DC Supply Current per Supply Pin or Ground Pin | $\pm 100$ | mA |
| $\mathrm{T}_{\text {STG }}$ | Storage Temperature Range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Lead Temperature, 1 mm from Case for 10 secs | 260 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{J}}$ | Junction Temperature Under Bias | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\mathrm{JA}}$ |  | $\begin{aligned} & 377 \\ & 320 \\ & 154 \end{aligned}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{P}_{\mathrm{D}}$ | $\begin{array}{lr}\text { Power Dissipation in Still Air } & \text { SC-88 } \\ \text { SC-74 } \\ & \text { UDFN6 }\end{array}$ | $\begin{aligned} & 332 \\ & 390 \\ & 812 \end{aligned}$ | mW |
| MSL | Moisture Sensitivity | Level 1 | - |
| $\mathrm{F}_{\mathrm{R}}$ | Flammability Rating Oxygen Index: 28 to 34 | UL 94 V-0 @ 0.125 in | - |
| $\mathrm{V}_{\text {ESD }}$ | ESD Withstand Voltage (Note 3) $\begin{array}{r}\text { Human Body Model } \\ \text { Charged Device Model }\end{array}$ | $\begin{aligned} & 2000 \\ & 1000 \end{aligned}$ | V |
| ILatchup | Latchup Performance (Note 4) | $\pm 100$ | mA |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.
2. Measured with minimum pad spacing on an FR4 board, using 10mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Characteristics |  | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive DC Supply Voltage |  | 1.65 | 5.5 | V |
| $\mathrm{V}_{\text {IN }}$ | DC Input Voltage |  | 0 | 5.5 | V |
| $\mathrm{V}_{\text {OUT }}$ | DC Output Voltage | Active-Mode (High or Low State) <br> Tri-State Mode (Note 1) <br> Power-Down Mode $\left(\mathrm{V}_{\mathrm{CC}}=0 \mathrm{~V}\right)$ | $\begin{aligned} & \hline 0 \\ & 0 \\ & 0 \end{aligned}$ | $\begin{aligned} & \hline \mathrm{V}_{\mathrm{CC}} \\ & 5.5 \\ & 5.5 \end{aligned}$ |  |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range |  | -55 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{tr}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise and Fall Time | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=1.65 \mathrm{~V} \text { to } 1.95 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{CC}}=2.3 \mathrm{~V} \text { to } 2.7 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{CC}}=3.0 \mathrm{~V} \text { to } 3.6 \mathrm{~V} \text { to } 5.5 \mathrm{~V} \end{gathered}$ | $\begin{aligned} & \hline 0 \\ & 0 \\ & 0 \\ & 0 \\ & \hline \end{aligned}$ | $\begin{gathered} 20 \\ 20 \\ 10 \\ 5 \end{gathered}$ | ns |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}$ <br> (V) | $\mathrm{T}_{\text {A }}=25^{\circ} \mathrm{C}$ |  |  | $-55^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 125^{\circ} \mathrm{C}$ |  | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max | Min | Max |  |
| $\mathrm{V}_{\mathrm{IH}}$ | High-Level Input Voltage (NLV) | - | 1.65 to 1.95 | $0.75 \times \mathrm{V}_{\mathrm{CC}}$ | - | - | $0.75 \times \mathrm{V}_{\mathrm{CC}}$ | - | V |
|  |  |  | 2.3 to 5.5 | $0.70 \times V_{C C}$ | - | - | $0.70 \times \mathrm{V}_{\text {CC }}$ | - |  |
|  | High-Level Input Voltage | - | 1.65 to 1.95 | $0.65 \times \mathrm{V}_{\mathrm{CC}}$ | - | - | $0.65 \times \mathrm{V}_{\mathrm{CC}}$ | - | V |
|  |  |  | 2.3 to 5.5 | $0.70 \times V_{C C}$ | - | - | $0.70 \times \mathrm{V}_{\mathrm{CC}}$ | - |  |
| $\mathrm{V}_{\text {IL }}$ | Low-Level Input Voltage (NLV) | - | 1.65 to 1.95 | - | - | $0.25 \times \mathrm{V}_{\mathrm{CC}}$ | - | $0.25 \times \mathrm{V}_{\mathrm{CC}}$ | V |
|  |  |  | 2.3 to 5.5 | - | - | $0.30 \times \mathrm{V}_{\mathrm{CC}}$ | - | $0.30 \times \mathrm{V}_{\mathrm{CC}}$ |  |
|  | Low-Level Input Voltage | - | 1.65 to 1.95 | - | - | $0.35 \times \mathrm{V}_{\mathrm{CC}}$ | - | $0.35 \times \mathrm{V}_{\mathrm{CC}}$ | V |
|  |  |  | 2.3 to 5.5 | - | - | $0.30 \times \mathrm{V}_{\mathrm{CC}}$ | - | $0.30 \times \mathrm{V}_{\mathrm{CC}}$ |  |
| $\mathrm{V}_{\mathrm{OH}}$ | High-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mathrm{I}_{\mathrm{OH}}=-100 \mu \mathrm{uA} \\ & \mathrm{I}_{\mathrm{OH}}=-4 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=-8 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=-16 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=-24 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=-32 \mathrm{~mA} \end{aligned}$ | $\begin{gathered} 1.65 \text { to } 5.5 \\ 1.65 \\ 2.3 \\ 3 \\ 3 \\ 4.5 \end{gathered}$ | $V_{\mathrm{CC}}-0.1$ 1.29 1.9 2.4 2.3 3.8 | $\begin{gathered} \mathrm{V}_{\mathrm{cc}} \\ 1.5 \\ 2.1 \\ 2.7 \\ 2.5 \\ 4 \end{gathered}$ |  | $\begin{gathered} \mathrm{V}_{\mathrm{Cc}}-0.1 \\ 1.29 \\ 1.9 \\ 2.4 \\ 2.3 \\ 3.8 \end{gathered}$ |  | V |
| $\mathrm{V}_{\text {OL }}$ | Low-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}} \mathrm{~V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mathrm{I}_{\mathrm{OH}}=100 \mathrm{\mu A} \\ & \mathrm{I}_{\mathrm{OH}}=4 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=8 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=16 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=24 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{OH}}=32 \mathrm{~mA} \end{aligned}$ | $\begin{gathered} 1.65 \text { to } 5.5 \\ 1.65 \\ 2.3 \\ 3 \\ 3 \\ 4.5 \end{gathered}$ |  | $\begin{aligned} & - \\ & 0.08 \\ & 0.12 \\ & 0.24 \\ & 0.26 \\ & 0.31 \end{aligned}$ | $\begin{gathered} 0.1 \\ 0.24 \\ 0.3 \\ 0.4 \\ 0.55 \\ 0.55 \end{gathered}$ |  | $\begin{gathered} 0.1 \\ 0.24 \\ 0.3 \\ 0.4 \\ 0.55 \\ 0.55 \end{gathered}$ | V |
| 1 N | Input Leakage Current | $\mathrm{V}_{1 \mathrm{I}}=5.5 \mathrm{~V}$ or GND | 1.65 to 5.5 | - | - | $\pm 0.1$ | - | $\pm 1.0$ | $\mu \mathrm{A}$ |
| IofF | Power Off Leakage Current | $\begin{aligned} & \mathrm{V}_{\text {IN }}=5.5 \mathrm{~V} \text { or } \\ & \mathrm{V}_{\text {OUT }}=5.5 \mathrm{~V} \end{aligned}$ | 0 | - | - | 1.0 | - | 10 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{CC}}$ | Quiescent Supply Current | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}}$ or GND | 5.5 | - | - | 1.0 | - | 10 | $\mu \mathrm{A}$ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}$ <br> (V) | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ |  |  | $-55^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{A}} \leq 125^{\circ} \mathrm{C}$ |  | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max | Min | Max |  |
| $\begin{aligned} & \mathrm{t}_{\mathrm{tPLH}}, \\ & \mathrm{t}_{\text {PHLL }} \end{aligned}$ | Propagation Delay, A to Y (Figures 2 and 3) | $\mathrm{R}_{\mathrm{L}}=1 \mathrm{M} \Omega, \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF}$ | 1.65 to 1.95 | - | 6.2 | 10.5 | - | 11.0 | ns |
|  |  | $\mathrm{R}_{\mathrm{L}}=1 \mathrm{M} \Omega, \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF}$ | 2.3 to 2.7 | - | 3.6 | 6.0 | - | 6.4 |  |
|  |  | $\mathrm{R}_{\mathrm{L}}=1 \mathrm{M} \Omega, \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF}$ | 3.0 to 3.6 | - | 2.9 | 4.1 | - | 4.5 |  |
|  |  | $\mathrm{R}_{\mathrm{L}}=500 \Omega, \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ |  | - | 3.2 | 5.1 | - | 5.4 |  |
|  |  | $\mathrm{R}_{\mathrm{L}}=1 \mathrm{M} \Omega, \mathrm{C}_{\mathrm{L}}=15 \mathrm{pF}$ | 4.5 to 5.5 | - | 2.4 | 3.2 | - | 3.5 |  |
|  |  | $\mathrm{R}_{\mathrm{L}}=500 \Omega, \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ |  | - | 2.7 | 4.0 | - | 4.3 |  |

CAPACITIVE CHARACTERISTICS

| Symbol | Parameter | Condition | Typical | Units |
| :---: | :--- | :--- | :---: | :---: |
| $\mathrm{C}_{\mathrm{IN}}$ | Input Capacitance | $\mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ | 2.5 | pF |
| $\mathrm{C}_{\mathrm{OUT}}$ | Output Capacitance | $\mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ | 2.5 | pF |
| $\mathrm{C}_{\mathrm{PD}}$ | Power Dissipation Capacitance <br> (Note 3) | $10 \mathrm{MHz}, \mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ <br> $10 \mathrm{MHz}, \mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ | 9 | pF |

5. $\mathrm{C}_{P D}$ is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{C C(O P R)}=C_{P D} \bullet V_{C C} \bullet f_{i n}+I_{C C} . C_{P D}$ is used to determine the no-load dynamic power consumption; $P_{D}=C_{P D} \bullet \mathrm{~V}_{\mathrm{CC}}{ }^{2} \bullet \mathrm{f}_{\mathrm{in}}+\mathrm{I}_{\mathrm{CC}} \bullet \mathrm{V}_{\mathrm{CC}}$.

$\mathrm{C}_{\mathrm{L}}$ includes probe and jig capacitance
$\mathrm{R}_{\mathrm{T}}$ is $\mathrm{Z}_{\text {OUT }}$ of pulse generator (typically $50 \Omega$ )
$\mathrm{f}=1 \mathrm{MHz}$
Figure 2. Test Circuit


Figure 3. Switching Waveforms

| $\mathbf{V}_{\mathbf{C C}}, \mathbf{v}$ | $\mathbf{V}_{\mathbf{m o}}, \mathbf{V}$ |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  |  |  | $\mathbf{t}_{\mathbf{P Z L}}, \mathbf{t}_{\mathbf{P L Z}}, \mathbf{t}_{\mathbf{P Z H}}, \mathbf{t}_{\mathbf{P H Z}}$ | $\mathbf{v}_{\mathbf{Y},} \mathbf{v}$ |
|  | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | 0.15 |
| 2.3 to 2.7 | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | 0.15 |
| 3.0 to 3.6 | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | 0.3 |
| 4.5 to 5.5 | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | $\mathrm{~V}_{\mathrm{CC}} / 2$ | 0.3 |

NL7SZ19

DEVICE ORDERING INFORMATION

| Device | Packages | Specific Device Code | Pin 1 Orientation <br> (See below) | Shipping ${ }^{\dagger}$ |
| :--- | :---: | :---: | :---: | :---: |
| NL7SZ19DFT2G | SC-88 | LE | Q4 | $3000 /$ Tape \& Reel |
| NLV7SZ19DFT2G* | SC-88 | LE | Q4 | $3000 /$ Tape \& Reel |
| NL7SZ19DBVT1G | SC-74 | AK | Q4 | $3000 /$ Tape \& Reel |
| NL7SZ19MUR2G** | UDFN6, 1.2 $\times 1.0,0.4 P$ | $U$ | Q2 | $3000 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.
** Please refer to NLV specifications for this device.
PIN 1 ORIENTATION IN TAPE AND REEL
Direction of Feed



RECOMMENDED SOLDERING FOOTPRINT*

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 2. CONTROLLING DIMENSION: MILLIMETERS.
2. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
3. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF DIMENSIONS D AND E1 AT THE OUT
THE PLASTIC BODY AND DATUM H.
THE PLASTIC BODY AND DATUM H.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE DIMENSIONS b AND c APPLY TO THE FLAT SEC
LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
6. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS |  |  | INCHES |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | -- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC |  |  | 0.026 BSC |  |  |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC |  |  | 0.006 BSC |  |  |
| aaa | 0.15 |  |  | 0.006 |  |  |
| bbb | 0.30 |  |  | 0.012 |  |  |
| ccc | 0.10 |  |  | 0.004 |  |  |
| ddd | 0.10 |  |  | 0.004 |  |  |
|  | GENERIC |  |  |  |  |  |
|  | MARKING DIAGRAM* |  |  |  |  |  |



XXX $=$ Specific Device Code
M = Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.


## STYLES ON PAGE 2

| DOCUMENT NUMBER: | 98ASB42985B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. <br> Printed versions are uncontroled except when stamped "CONTROLLED COPY" in red. |
| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SC-88/SC70-6/SOT-363 | PAGE 1 OF 2 |

[^0] rights of others.

## SC-88/SC70-6/SOT-363

CASE 419B-02
ISSUE Y
STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 19:
PIN 1. IOUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF
STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1
STYLE 2:

CANCELLED
STYLE 8:
CANCELLED

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR
STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAAN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

| STYLE 3 : CANCELLED | STYLE 4: <br> PIN 1. CATHODE <br> 2. CATHODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. ANODE | STYLE 5: <br> PIN 1. ANODE <br> 2. ANODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. CATHODE | STYLE 6 : <br> PIN 1. ANODE 2 <br> 2. $\mathrm{N} / \mathrm{C}$ <br> 3. CATHODE 1 <br> 4. ANODE 1 <br> 5. N/C <br> 6. CATHODE 2 |
| :---: | :---: | :---: | :---: |
| STYLE 9: | STYLE 10: | STYLE 11: | STYLE 12: |
| PIN 1. EMITTER 2 | PIN 1. SOURCE 2 | PIN 1. CATHODE 2 | PIN 1. ANODE 2 |
| 2. EMITTER 1 | 2. SOURCE 1 | 2. CATHODE 2 | 2. ANODE 2 |
| 3. COLLECTOR 1 | 3. GATE 1 | 3. ANODE 1 | 3. CATHODE 1 |
| 4. BASE 1 | 4. DRAIN 1 | 4. CATHODE 1 | 4. ANODE 1 |
| 5. BASE 2 | 5. DRAIN 2 | 5. CATHODE 1 | 5. ANODE 1 |
| 6. COLLECTOR 2 | 6. GATE 2 | 6. ANODE 2 | 6. CATHODE 2 |
| STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: |
| PIN 1. ANODE 1 | PIN 1. BASE 1 | PIN 1. BASE 1 | PIN 1. VIN1 |
| 2. ANODE 2 | 2. EMITTER 2 | 2. EMITTER 1 | 2. VCC |
| 3. ANODE 3 | 3. COLLECTOR 2 | 3. COLLECTOR 2 | 3. VOUT2 |
| 4. CATHODE 3 | 4. BASE 2 | 4. BASE 2 | 4. VIN2 |
| 5. CATHODE 2 | 5. EMITTER 1 | 5. EMITTER 2 | 5. GND |
| 6. CATHODE 1 | 6. COLLECTOR 1 | 6. COLLECTOR 1 | 6. VOUT1 |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: |
| PIN 1. ANODE 1 | PIN 1. D1 (i) | PIN 1. Vn | PIN 1. CATHODE |
| 2. $\mathrm{N} / \mathrm{C}$ | 2. GND | 2. CH 1 | 2. ANODE |
| 3. ANODE 2 | 3. D2 (i) | 3. Vp | 3. CATHODE |
| 4. CATHODE 2 | 4. D2 (c) | 4. N/C | 4. CATHODE |
| 5. N/C | 5. VBUS | 5. CH 2 | 5. CATHODE |
| 6. CATHODE 1 | 6. D1 (c) | 6. N/C | 6. CATHODE |
| STYLE 27: | STYLE 28: | STYLE 29: | STYLE 30: |
| PIN 1. BASE 2 | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. SOURCE 1 |
| 2. BASE 1 | 2. DRAIN | 2. ANODE | 2. DRAIN 2 |
| 3. COLLECTOR 1 | 3. GATE | 3. COLLECTOR | 3. DRAIN 2 |
| 4. EMITTER 1 | 4. SOURCE | 4. EMITTER | 4. SOURCE 2 |
| 5. EMITTER 2 | 5. DRAIN | 5. BASE/ANODE | 5. GATE 1 |
| 6. COLLECTOR 2 | 6. DRAIN | 6. CATHODE | 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SC-88/SC70-6/SOT-363 | PAGE 2 OF 2 |

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UDFN6, 1.2x1.0, 0.4P
CASE 517AA-01
ISSUE D
DATE 03 SEP 2010

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 mm FROM TERMINAL
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

|  | MILLIMETERS |  |
| :---: | :---: | :---: |
| DIM | MIN | MAX |
| A | 0.45 | 0.55 |
| A1 | 0.00 | 0.05 |
| A3 | 0.127 |  |
| REF |  |  |
| b | 0.15 |  |
| D | 1.20 |  |
| BSC |  |  |
| E | 1.00 |  |
| BSC |  |  |
| e | 0.40 |  |
| BSC |  |  |
| L | 0.30 | 0.40 |
| L1 | 0.00 | 0.15 |
| L2 | 0.40 | 0.50 |

Side View (Optional)

GENERIC
MARKING DIAGRAM*


X = Specific Device Code
M = Date Code
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, " G " or microdot " $\mathrm{\bullet}$ ", may or may not be present.

## MOUNTING FOOTPRINT*


*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | 6 PIN UDFN, 1.2X1.0, 0.4P | PAGE 1 OF 1 |

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